Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A method comprising:

forming a first electrode and a second electrode on a base body; and

chemically etching at least a portion of the base body with an etching solution comprising an acid to adjust a resistance of the base body between the first electrode and the second electrode, wherein the first and second electrodes are made from a material that is not ~~etched~~ etchable by the etching solution or that is ~~etched~~ etchable, by the etching solution, less than the base body is ~~etched~~etchable by the etching solution.

2. (Original) The method of claim 1, wherein the base body comprises a ceramic material.

3. (Original) The method of claim 1, wherein the base body comprises a material having a resistance with a negative temperature coefficient.

4. (Original) The method of claim 1, wherein a length of an edge of the base body is less than about 3 mm.

5. (Original) The method of claim 1, wherein chemically etching at least a portion of the base body comprises immersing the base body in an etching liquid.

6. (Currently Amended) The method of claim [[5]]1, wherein the ~~etching liquid comprises~~ acid is sulfuric acid.

7. (Original) The method of claim 1, further comprising measuring a value of a resistance of the base body prior to chemically etching the at least a portion of the base body.

8. (Canceled)

9. (Original) The method of claim 1, further comprising:

determining a difference between the predetermined value and a measured value of the resistance; and

determining a duration for the chemically etching based on said difference, wherein chemically etching at least a portion of the base body comprises chemically etching at least a portion of the base body for the duration.

10. (Original) The method of claim 1, wherein forming the first electrode and the second electrode on the base body comprises forming the first electrode at a location opposite the second electrode on the base body.

11. (Original) The method of claim 1, wherein chemically etching at least a portion of the base body to adjust the resistance of the base body comprises chemically etching at least a portion of the base body to adjust the resistance of the base body to a predetermined value.

12. (New) The method of claim 1, wherein the first and second electrodes comprise a multilayer metallization comprising a Ag/Ni/Sn layer sequence.

13. (New) The method of claim 1, wherein the first and second electrodes comprise a silver/palladium metallization.

14. (New) A method comprising:

forming a first electrode and a second electrode on a base body; and

chemically etching at least a portion of the base body with an etching solution to adjust a resistance of the base body between the first electrode and the second electrode, wherein the first and second electrodes comprise a multilayer metallization comprising a Ag/Ni/Sn layer sequence.

15. (New) A method comprising:

forming a first electrode and a second electrode on a base body; and

chemically etching at least a portion of the base body with an etching solution to adjust a resistance of the base body between the first electrode and the second electrode, wherein the first and second electrodes comprise a silver/palladium metallization.